L Number	Hits	Search Text	DB	Time stamp
1	530	((multi\$1layer\$3 multiple\$1layer\$3 double\$1layer\$3 two\$1layer\$3	USPAT;	2003/12/30 20:55
		triple\$11ayer\$2)near7(source and drain))	US-PGPUB	
2	296	(((multi\$1layer\$3 multiple\$1layer\$3 double\$1layer\$3 two\$1layer\$3	USPAT;	2003/12/30 20:55
		triple\$1layer\$2)near7(source and drain))) and(thin adj film adj	US-PGPUB	
		transistor\$2 tft lcd soi display\$2 silicon adj insulator\$2)		
3	238	((contact via through) adj3(hole\$2)) and ((((multi\$1layer\$3	USPAT;	2003/12/30 21:02
		multiple\$11ayer\$3 double\$11ayer\$3 two\$11ayer\$3	US-PGPUB	
		triple\$1layer\$2)near7(source and drain))) and(thin adj film adj	•	
		transistor\$2 tft lcd soi display\$2 silicon adj insulator\$2))		
4	172	((molybdenum MO chrom\$4 cr tantalum ta tungsten	USPAT;	2003/12/30 21:00
		titanium)near21(aluminum))and (((contact via through) adj3(hole\$2))	US-PGPUB	
		and ((((multi\$1layer\$3 multiple\$1layer\$3 double\$1layer\$3		
		two\$1layer\$3 triple\$1layer\$2)near7(source and drain))) and(thin adj film		
		adj transistor\$2 tft lcd soi display\$2 silicon adj insulator\$2)))		
5	187	((multi\$1layer\$3 multiple\$1layer\$3 double\$1layer\$3 two\$1layer\$3	ЕРО; ЈРО;	2003/12/30 20:55
		triple\$1layer\$2)near7(source and drain))	DERWENT	
6	51	(((multi\$11ayer\$3 multiple\$11ayer\$3 double\$11ayer\$3 two\$11ayer\$3	EPO; JPO;	2003/12/30 20:56
		triple\$1layer\$2)near7(source and drain))) and(thin adj film adj	DERWENT	
		transistor\$2 tft lcd soi display\$2 silicon adj insulator\$2)		
7	7	((contact via through) adj3(hole\$2)) and ((((multi\$1layer\$3	EPO; JPO;	2003/12/30 20:56
		multiple\$1layer\$3 double\$1layer\$3 two\$1layer\$3	DERWENT	
		triple\$1layer\$2)near7(source and drain))) and(thin adj film adj		
		transistor\$2 tft lcd soi display\$2 silicon adj insulator\$2))		
8	2	((molybdenum MO chrom\$4 cr tantalum ta tungsten	EPO; JPO;	2003/12/30 21:00
		titanium)near21(aluminum))and ((((multi\$1layer\$3 multiple\$1layer\$3	DERWENT	
		double\$1layer\$3 two\$1layer\$3 triple\$1layer\$2)near7(source and drain)))		
		and(thin adj film adj transistor\$2 tft lcd soi display\$2 silicon adj		
		insulator\$2))	1100.17	2002/12/20 21 00
9	169	(steep step\$2 deep)and (((molybdenum MO chrom\$4 cr tantalum ta	USPAT;	2003/12/30 21:08
		tungsten titanium)near21(aluminum))and (((contact via through) adj3(US-PGPUB	
		hole\$2)) and ((((multi\$11ayer\$3 multiple\$11ayer\$3 double\$11ayer\$3		
		two\$1layer\$3 triple\$1layer\$2)near7(source and drain))) and(thin adj film		
4.0		adj transistor\$2 tft lcd soi display\$2 silicon adj insulator\$2))))	LICDATE	2002/12/20 21-01
10	8	(deep)and (((molybdenum MO chrom\$4 cr tantalum ta tungsten	USPAT;	2003/12/30 21:01
		titanium)near21(aluminum))and (((contact via through) adj3(hole\$2))	US-PGPUB	
		and ((((multi\$1layer\$3 multiple\$1layer\$3 double\$1layer\$3		
		two\$1layer\$3 triple\$1layer\$2)near7(source and drain))) and(thin adj film		
		adj transistor\$2 tft lcd soi display\$2 silicon adj insulator\$2))))	LICDATE	2002/12/20 21-02
11	22	(((contact via through) adj3(hole\$2))near31(steep step\$2 deep)) and ((USPAT;	2003/12/30 21:02
		((multi\$1layer\$3 multiple\$1layer\$3 double\$1layer\$3 two\$1layer\$3	US-PGPUB	
		triple\$1layer\$2)near7(source and drain))) and(thin adj film adj		
1.2		transistor\$2 tft lcd soi display\$2 silicon adj insulator\$2))	LICDAT.	2002/12/20 21:00
12	9	(steep)and (((molybdenum MO chrom\$4 cr tantalum ta tungsten	USPAT;	2003/12/30 21:09
		titanium)near21(aluminum))and (((contact via through) adj3(hole\$2))	US-PGPUB	
		and ((((multi\$1layer\$3 multiple\$1layer\$3 double\$1layer\$3		
		two\$1layer\$3 triple\$1layer\$2)near7(source and drain))) and(thin adj film		
	1	adj transistor\$2 tft lcd soi display\$2 silicon adj insulator\$2))))		